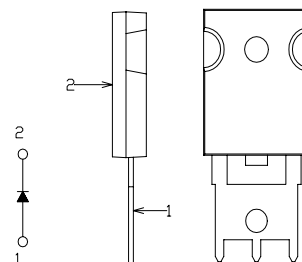


FRD Type : KSF30A20E

■ OUTLINE DRAWING

構造 : 拡散型シリコンダイオード(F R D)
Construction: Diffusion-type Silicon Diode

用途 : 高周波整流用
Application : High Frequency Rectification



■ 最大定格 / Maximum Ratings

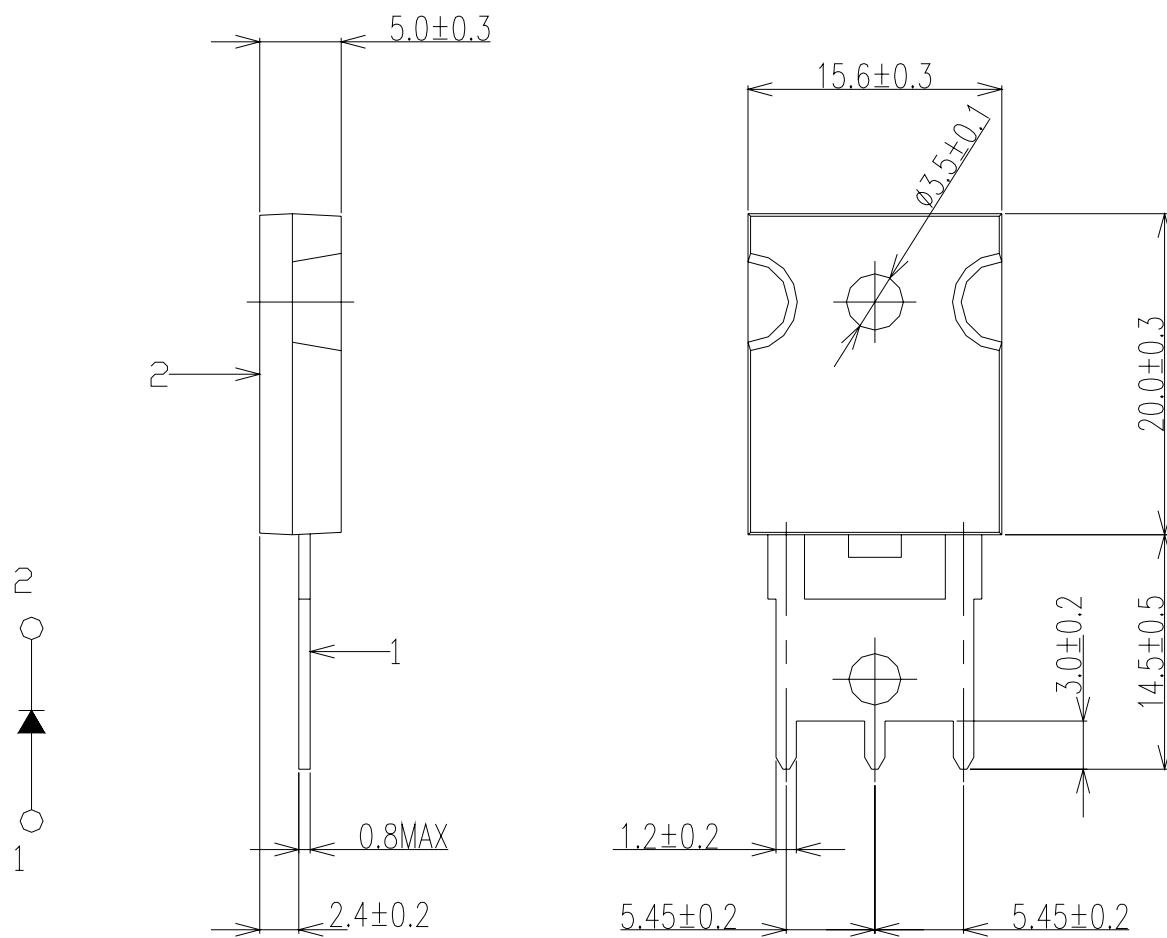
Approx Net Weight:6g

Rating	Symbol	KSF30A20E			Unit
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V_{RRM}	200			V
平均整流電流 Average Rectified Output Current	I_O	30	Tc=101	50 Hz、正弦半波通電抵抗負荷 Half Sine Wave Resistive Load	A
実効順電流 RMS Forward Current	$I_{F(RMS)}$	47			A
サージ順電流 Surge Forward Current	I_{FSM}	400	50 Hz 正弦半波, 1サイクル, 非くり返し Half Sine Wave, 1cycle, Non-repetitive		A
動作接合温度範囲 Operating Junction Temperature Range	T_{jw}	- 40 ~ + 150			
保存温度範囲 Storage Temperature Range	T_{stg}	- 40 ~ + 150			
締め付けトルク Mounting torque		0.5	推奨値 Recommended value		N・m

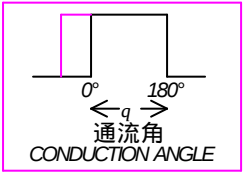
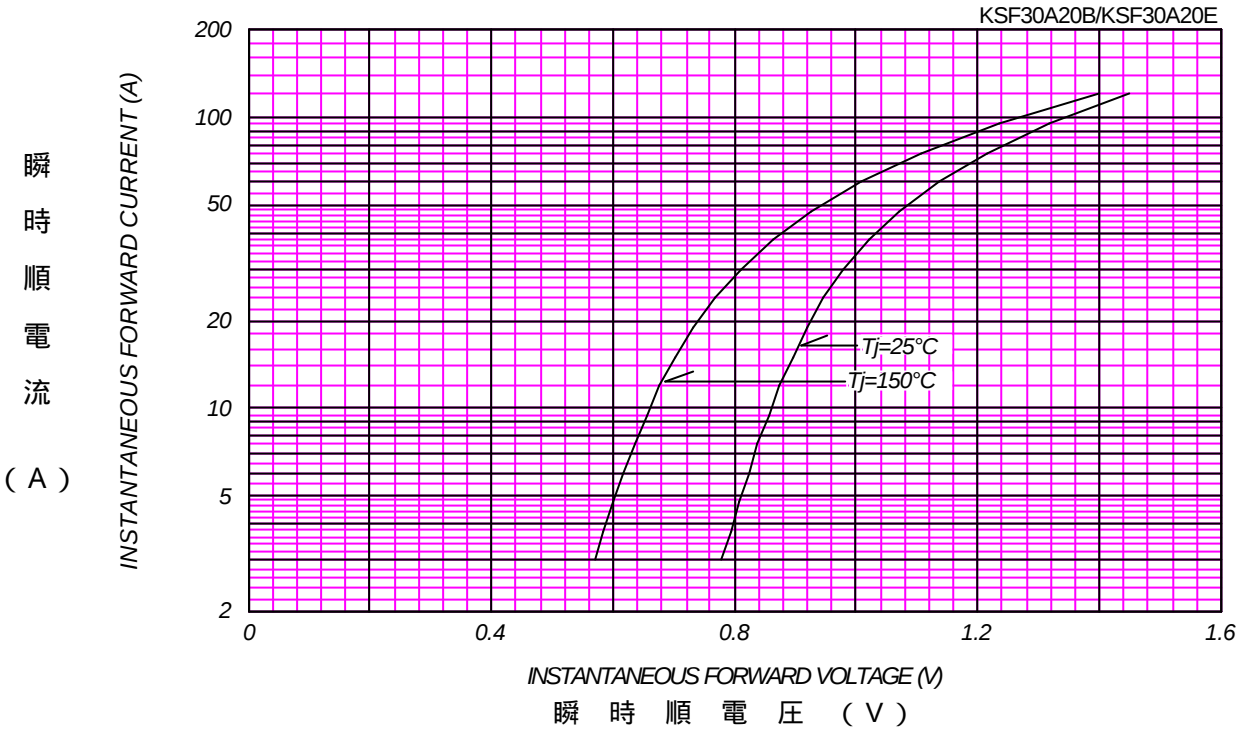
■ 電氣的・熱的特性 / Electrical・Thermal Characteristics

Characteristics	Symbol	Conditions	Mni.	Typ.	Max.	Unit
ピーク逆電流 Peak Reverse Current	I_{RM}	$T_j = 25$, $V_{RM} = V_{RRM}$	-	-	25	μA
ピーク順電圧 * Peak Forward Voltage	V_{FM}	$T_j = 25$, $I_{FM} = 30 A$	-	-	0.98	V
逆回復時間 Reverse Recovery Time	t_{rr}	$I_{FM} = 10 A$, -di/dt= 50 A/ μs , $T_a = 25$	-	-	50	ns
熱抵抗 Thermal Resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to Case	-	-	1.4	/W

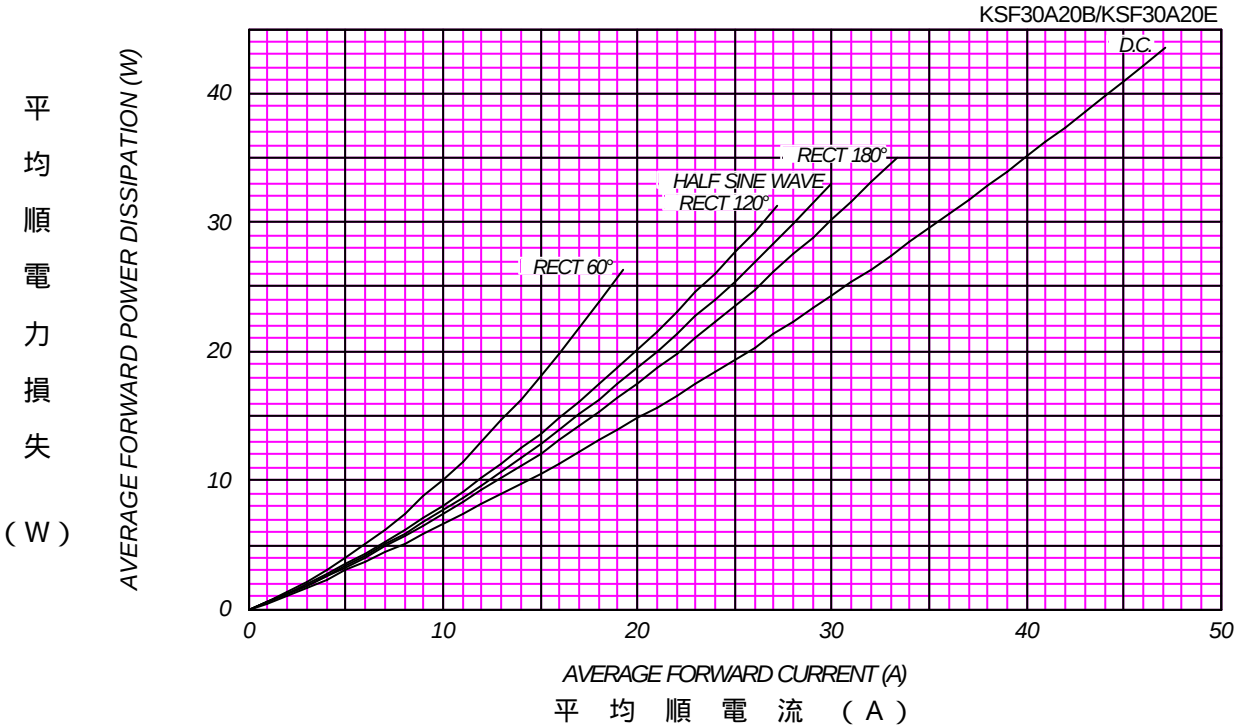
K S F 3 0 A 2 0 E外形図 (mm)

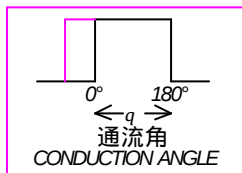


順電壓特性
FORWARD CURRENT VS. VOLTAGE

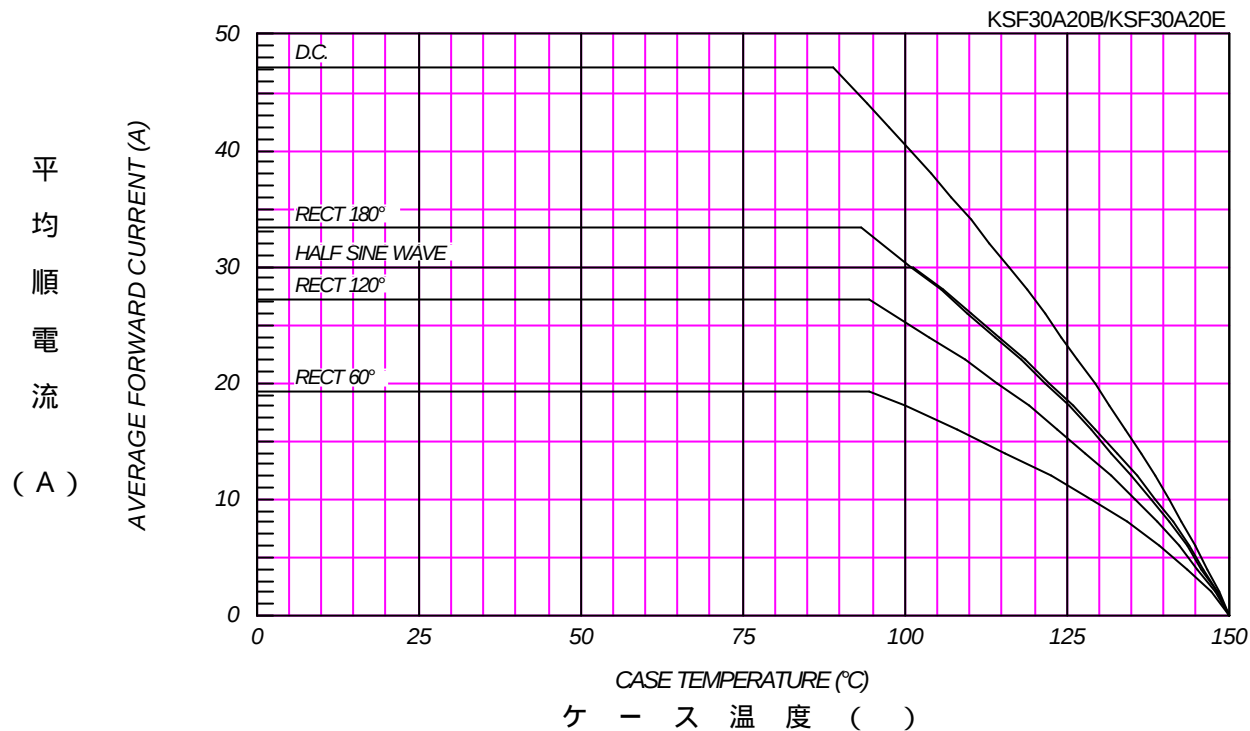


平均順電力損失特性
AVERAGE FORWARD POWER DISSIPATION





平均順電流 - ケース温度定格 AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE



サージ順電流定格 SURGE CURRENT RATINGS

f=50Hz, Half Sine Wave, Non-Repetitive, No Load

